
2SB861

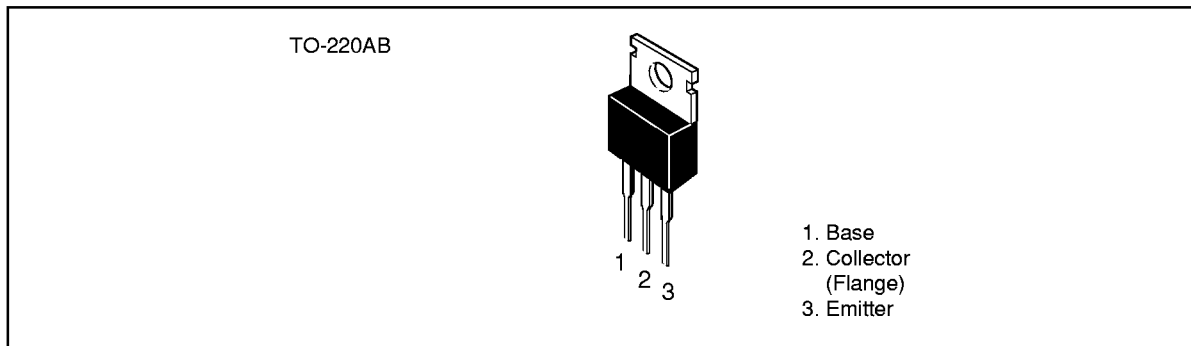
Silicon PNP Triple Diffused

HITACHI

Application

Low frequency power amplifier color TV vertical deflection output complementary pair with 2SD1138

Outline



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Item	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	-200	V
Collector to emitter voltage	V_{CEO}	-150	V
Emitter to base voltage	V_{EBO}	-6	V
Collector current	I_{c}	-2	A
Collector peak current	$I_{\text{C(peak)}}$	-5	A
Collector power dissipation	P_{c}	1.8	W
	P_{c}^{*1}	30	W
Junction temperature	T_{j}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-45 to +150	$^\circ\text{C}$

Note: 1. Value at $T_{\text{c}} = 25^\circ\text{C}$

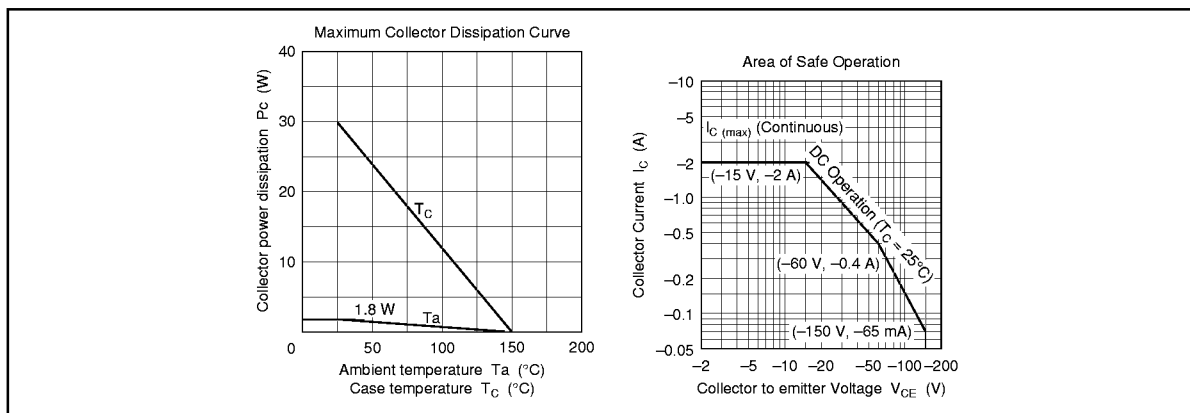
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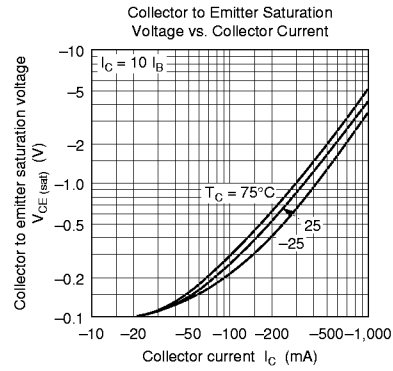
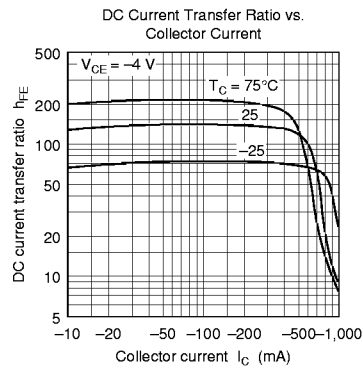
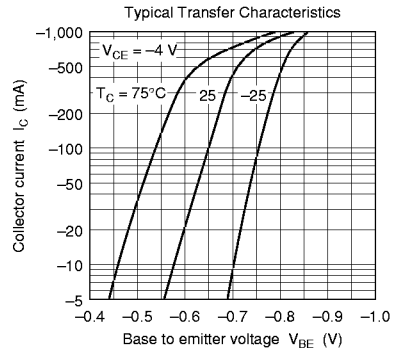
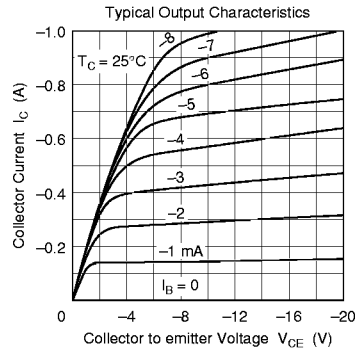
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CBO}$	-150	—	—	V	$I_C = -50 \text{ mA}$, $R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-6	—	—	V	$I_E = -5 \text{ mA}$, $I_C = 0$
Collector cutoff current	I_{CBO}	—	—	-1	μA	$V_{CB} = -120 \text{ V}$, $I_E = 0$
DC current transfer ratio	h_{FE1}^{*1}	60	—	200		$V_{CE} = -4 \text{ V}$, $I_C = -50 \text{ mA}$
	h_{FE2}	60	—	—		$V_{CE} = -10 \text{ V}$, $I_C = -500 \text{ mA}^{*2}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	-3	V	$I_C = -500 \text{ mA}$, $I_B = -50 \text{ mA}$
Base to emitter voltage	V_{BE}	—	—	-1	V	$V_{CE} = -4 \text{ V}$, $I_C = -50 \text{ mA}$
Collector output capacitance	C_{ob}	—	30	—	pF	$V_{CB} = -100 \text{ V}$, $I_E = 0$, $f = 1 \text{ MHz}$

Notes: 1. The 2SB861 is grouped by h_{FE1} as follows.
2. Pulse test

B	C
60 to 120	100 to 200





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